

Silicon PNP Power Transistor

2SA770

DESCRIPTION

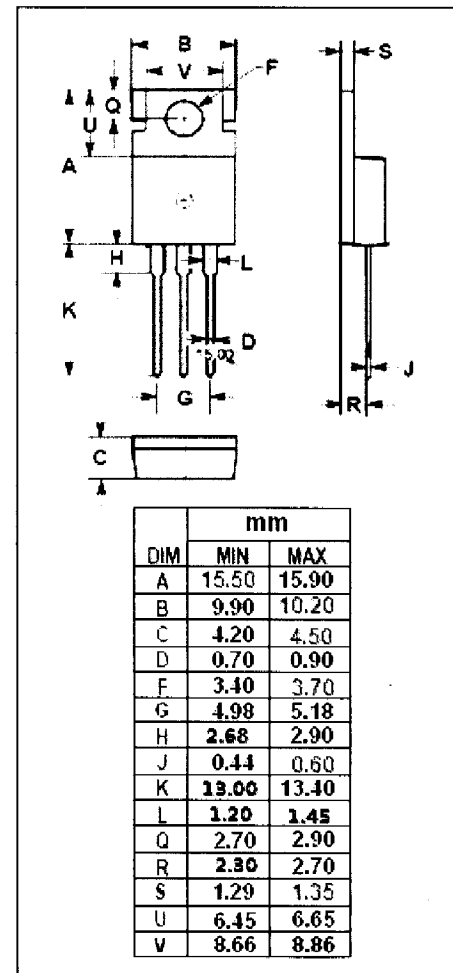
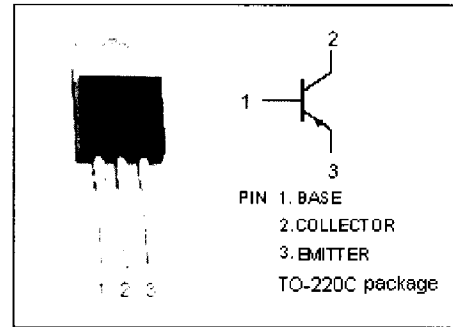
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -60(V)(Min.)$
- Complement to Type 2SC1985

APPLICATIONS

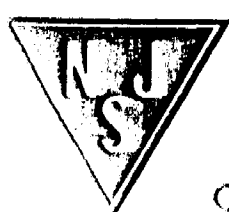
- Designed for audio and general purpose applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-6	A
I_B	Base Collector Current-Continuous	-3	A
P_C	Total Power Dissipation @ $T_c=25^{\circ}C$	40	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



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ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -25\text{mA}; I_B = 0$	-60			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -3\text{A}; I_B = -0.3\text{A}$			-1.0	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -60\text{V}; I_E = 0$			-1.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -6\text{V}; I_C = 0$			-1.0	mA
h_{FE}	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -4\text{V}$	40			
f_T	Current-Gain—Bandwidth Product	$I_E = 0.5\text{A}; V_{CE} = -12\text{V}$		10		MHz

Switching Times

t_r	Rise Time	$I_C = -3\text{A}, R_L = 3\Omega,$ $I_{B1} = -I_{B2} = -0.4\text{A}, V_{CC} = -9\text{V}$		0.9		μs
t_{stg}	Storage Time			1.0		μs
t_f	Fall Time			0.1		μs